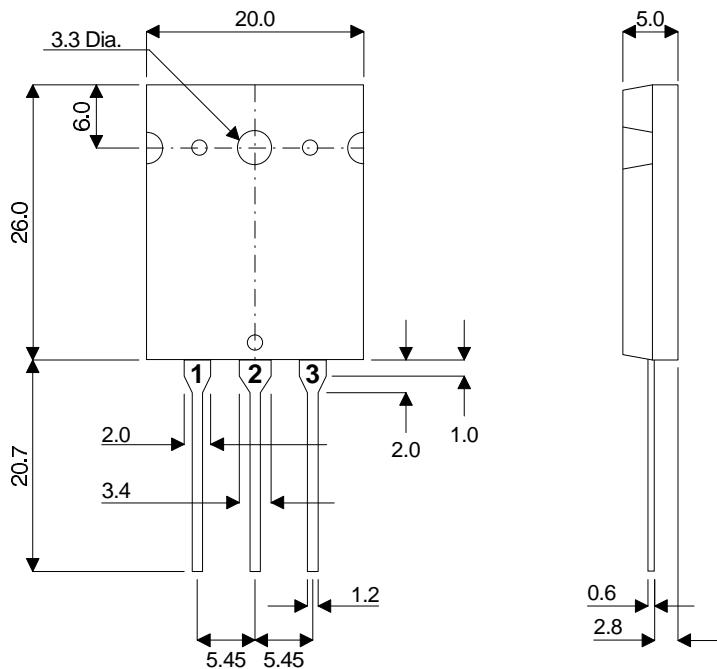

MECHANICAL DATA

Dimensions in mm


TO-3PBL

Pin 1 – Gate

Pin 2 – Source

Pin 3 – Drain

Case – Source

**N-CHANNEL
POWER MOSFET**
**POWER MOSFETS FOR
AUDIO APPLICATIONS**
FEATURES

- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (220V & 250V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODES
- COMPLIMENTARY P-CHANNEL
BUZ907DP & BUZ908DP

ABSOLUTE MAXIMUM RATINGS
(T_{case} = 25°C unless otherwise stated)

		BUZ902DP	BUZ903DP
V _{DSX}	Drain – Source Voltage	220V	250V
V _{GSS}	Gate – Source Voltage	±14V	
I _D	Continuous Drain Current	16A	
I _{D(PK)}	Body Drain Diode	16A	
P _D	Total Power Dissipation @ T _{case} = 25°C	250W	
T _{stg}	Storage Temperature Range	-55 to 150°C	
T _j	Maximum Operating Junction Temperature	150°C	
R _{θJC}	Thermal Resistance Junction – Case	0.5°C/W	

STATIC CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV_{DSX}	$V_{GS} = -10\text{V}$ $I_D = 10\text{mA}$	BUZ902DP	220			V
		BUZ903DP	250			V
BV_{GSS}	$V_{DS} = 0$	$I_G = \pm 100\mu\text{A}$	± 14			V
$V_{GS(\text{OFF})}$	$V_{DS} = 10\text{V}$	$I_D = 100\text{mA}$	0.10		1.5	V
$V_{DS(\text{SAT})}^*$	$V_{GD} = 0$	$I_D = 16\text{A}$			12	V
$R_{DS(\text{on})}^*$	$V_{GS} = 10$	$I_D = 16\text{A}$			0.75	Ω
I_{DSX}	$V_{GS} = -10\text{V}$	$V_{DS} = 220\text{V}$ BUZ902DP			10	mA
		$V_{DS} = 250\text{V}$ BUZ903DP			10	mA
yfs^*	$V_{DS} = 10\text{V}$	$I_D = 3\text{A}$	1.4		4	S

DYNAMIC CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{iss}	$V_{DS} = 10\text{V}$ $f = 1\text{MHz}$			TBA		pF
C_{oss}				TBA		
C_{rss}				TBA		
t_{on}	$V_{DS} = 20\text{V}$ $I_D = 7\text{A}$			TBA		ns
t_{off}				TBA		

* Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

